FORMING METHOD OF OXIDE FILM

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Abstract of **JP 11307526 (A)**

PROBLEM TO BE SOLVED: To provide a method forming a very thin oxide film by low pressure oxidizing in which film thickness is controlled properly. SOLUTION: A method forming an SiO2 film on an So substrate by introducing O2 on the Si substrate contains a process for setting an So substrate 1 in a heating furnace 10, a process for introducing N2 in the furnace 10, a process for introducing O2 in the furnace 10 and maintaining a constant oxidizing pressure, a process for raising the temperature up to a constant oxidizing temperature, while the oxidizing pressure is kept constant, a process for maintaining the above constant oxidizing temperature for a constant oxidizing period, while the oxidizing pressure is kept constant, and a process introducing N2 in the furnace 10 at the same time, when temperature fall is started after the above constant period has passed, replacing the inside of the furnace by N2 , and maintaining a constant pressure higher than the oxidizing pressure until the temperature on the furnace drops almost to the room temperature.